



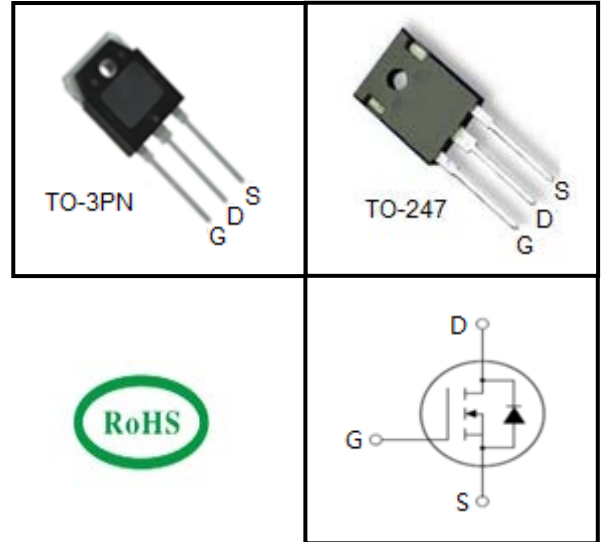
# 700V Super-Junction Power MOSFET

## FEATURES

- Very low FOM  $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

## APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
TPV70R110C	TO-3PN	70R110C
TPW70R110C	TO-247	70R110C

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	700	V
Continuous Drain Current	$I_D$	47	A
Pulsed Drain Current (note1)	$I_{DM}$	141	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	1120	mJ
Avalanche Current (note1)	$I_{AR}$	15	A
Repetitive Avalanche Energy (note1)	$E_{AR}$	1.76	mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	390	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	0.32	K/W
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62	



Specifications $T_J = 25^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 700V, V_{GS} = 0V, T_J = 25^{\circ}\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 700V, V_{GS} = 0V, T_J = 150^{\circ}\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	--	0.08	0.11	$\Omega$
Forward Transconductance (Note3)	$g_{fs}$	$V_{DS} = 10V, I_D = 20A$	--	40	--	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 50V,$ $f = 1.0\text{MHz}$	--	5100	--	$\mu F$
Output Capacitance	$C_{oss}$		--	225	--	
Reverse Transfer Capacitance	$C_{rss}$		--	6.2	--	
Total Gate Charge	$Q_g$	$V_{DD} = 560V, I_D = 47A,$ $V_{GS} = 10V$	--	90	--	nC
Gate-Source Charge	$Q_{gs}$		--	24	--	
Gate-Drain Charge	$Q_{gd}$		--	30	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 26A,$ $R_G = 1.7\Omega$	--	16	--	ns
Turn-on Rise Time	$t_r$		--	12	--	
Turn-off Delay Time	$t_{d(off)}$		--	83	--	
Turn-off Fall Time	$t_f$		--	5	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^{\circ}\text{C}$	--	--	47	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	141	
Body Diode Voltage	$V_{SD}$	$T_J = 25^{\circ}\text{C}, I_{SD} = 47A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_F = 26A,$ $di_F/dt = 100A/\mu s$	--	720	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	19	--	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		--	52	--	A

**Notes**

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2.  $I_{AS} = 15A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

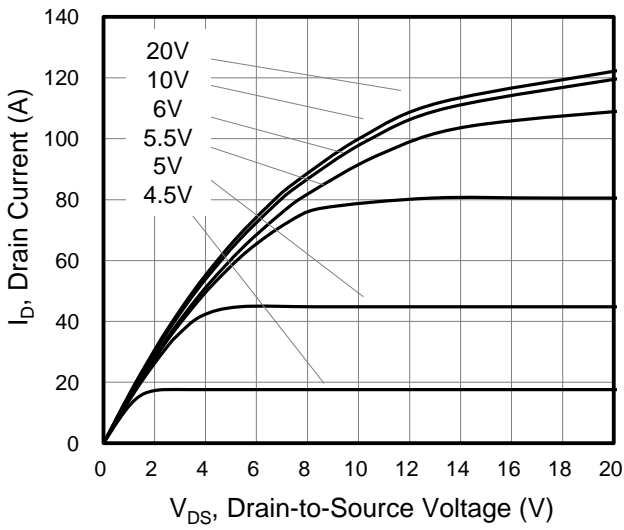


Figure 2. Transfer Characteristics

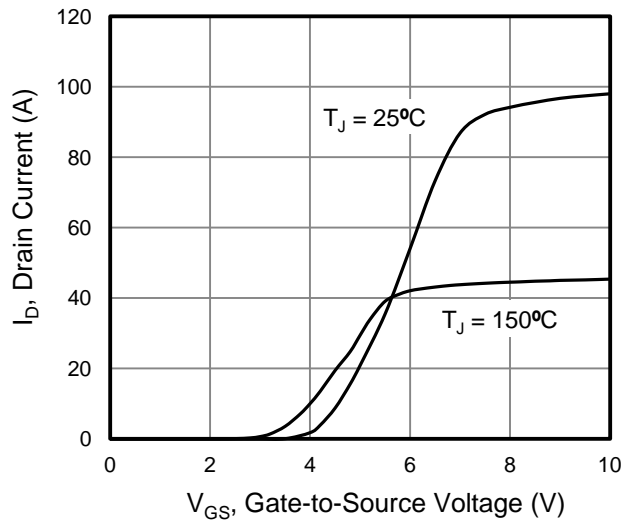


Figure 3. On-Resistance vs. Drain Current

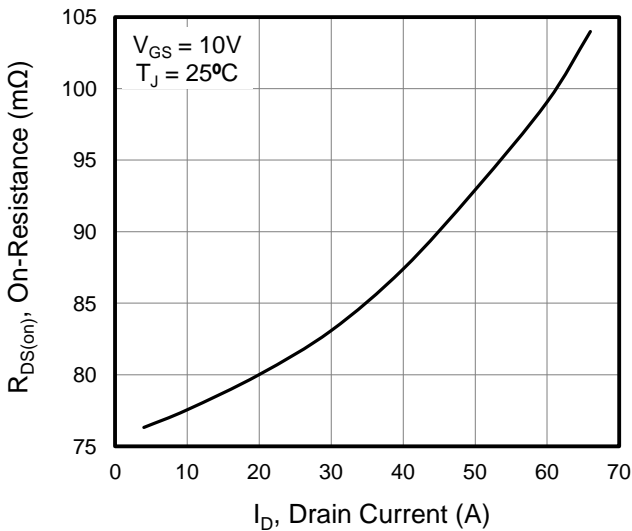


Figure 4. Capacitance

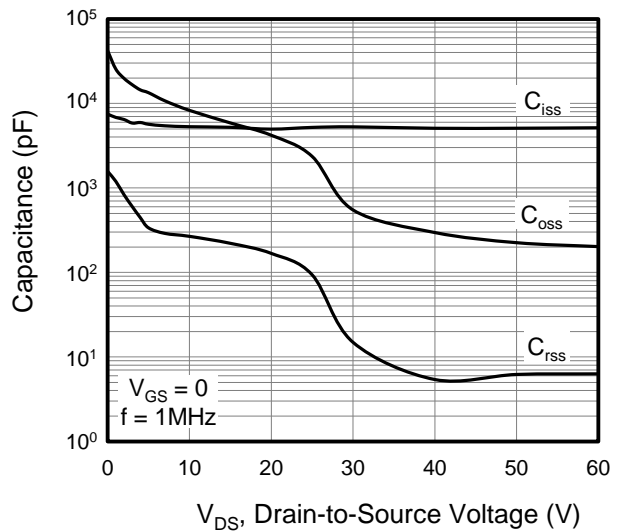


Figure 5. Gate Charge

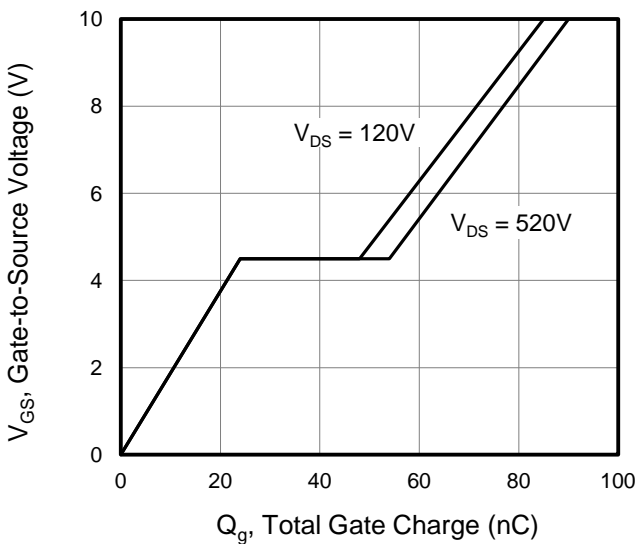
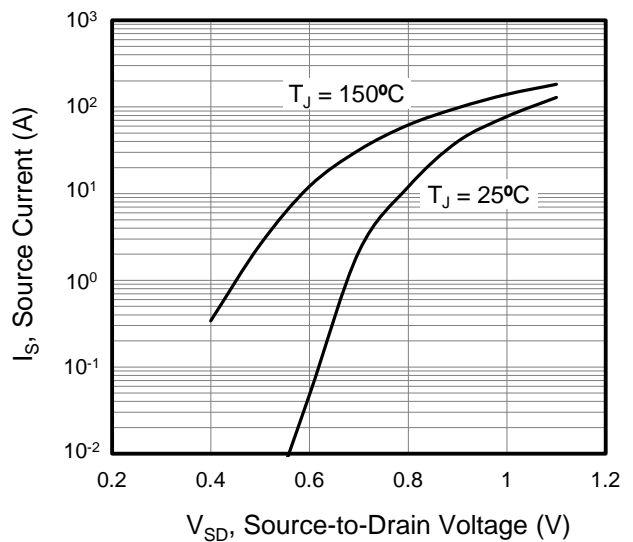


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Temperature

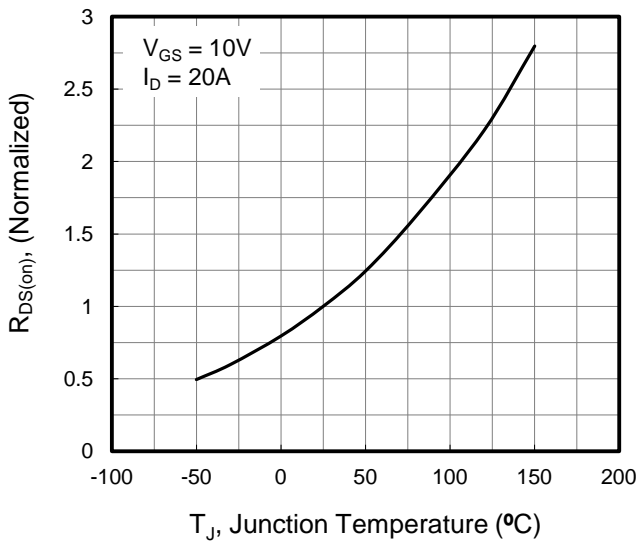


Figure 8. Threshold Voltage vs. Temperature

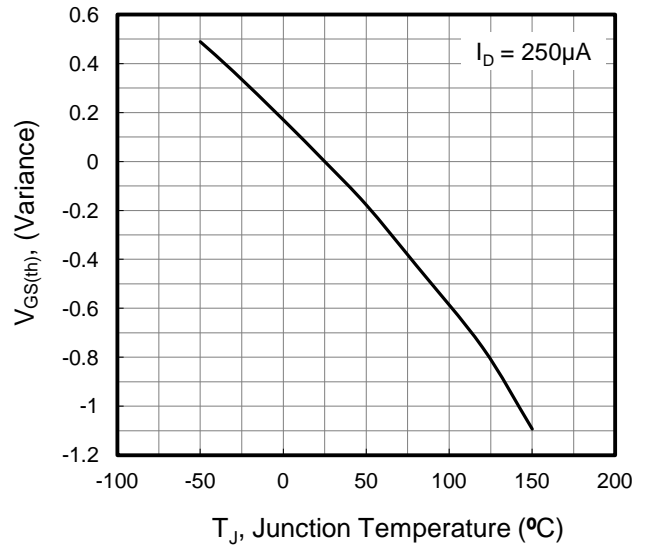


Figure 9. Transient Thermal Impedance

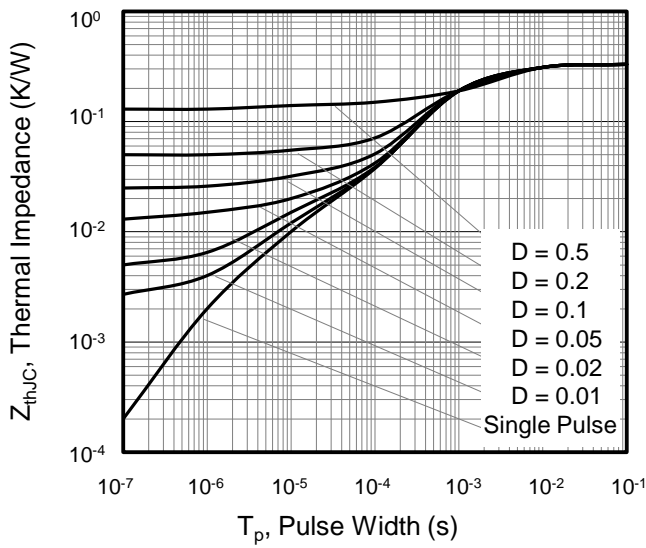




Figure A: Gate Charge Test Circuit and Waveform

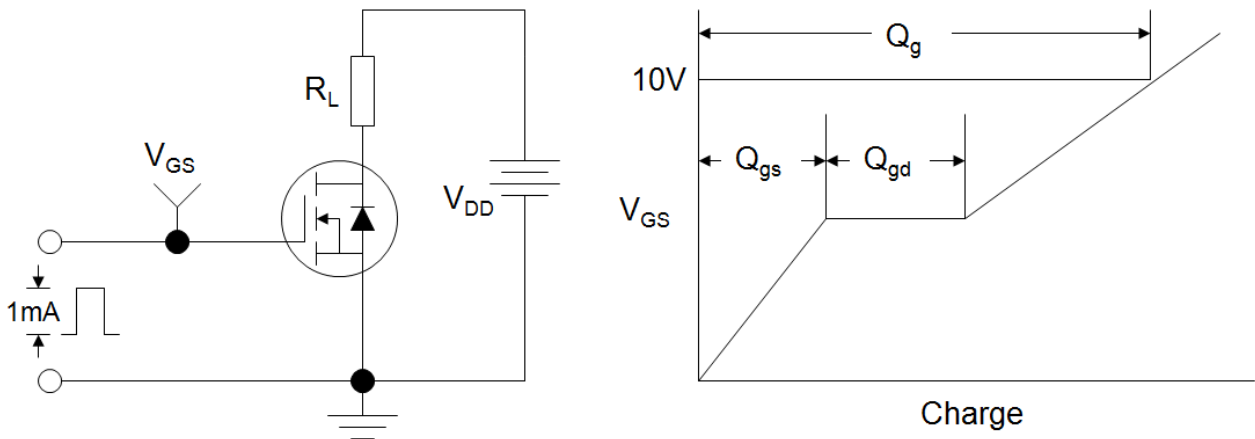


Figure B: Resistive Switching Test Circuit and Waveform

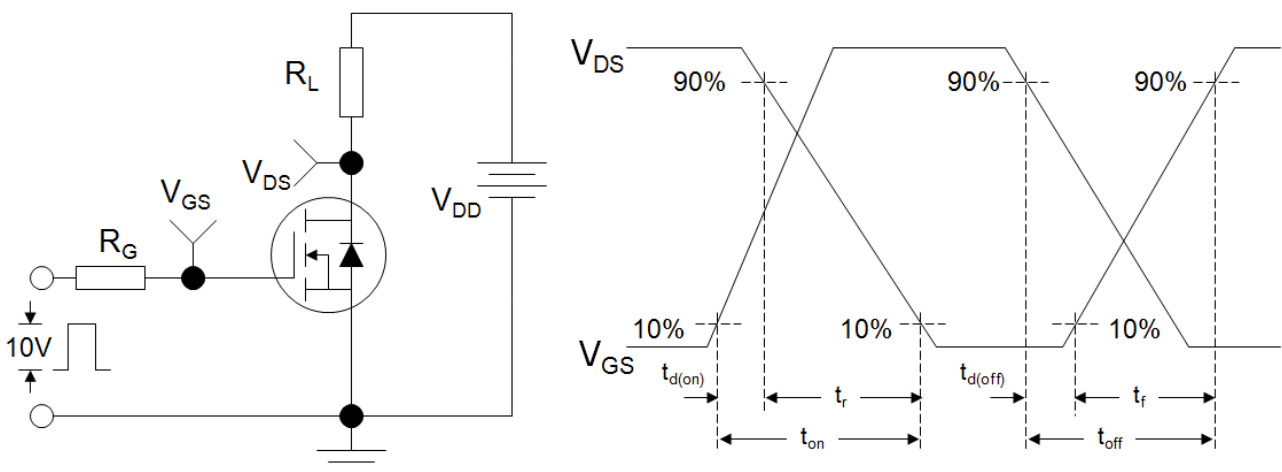
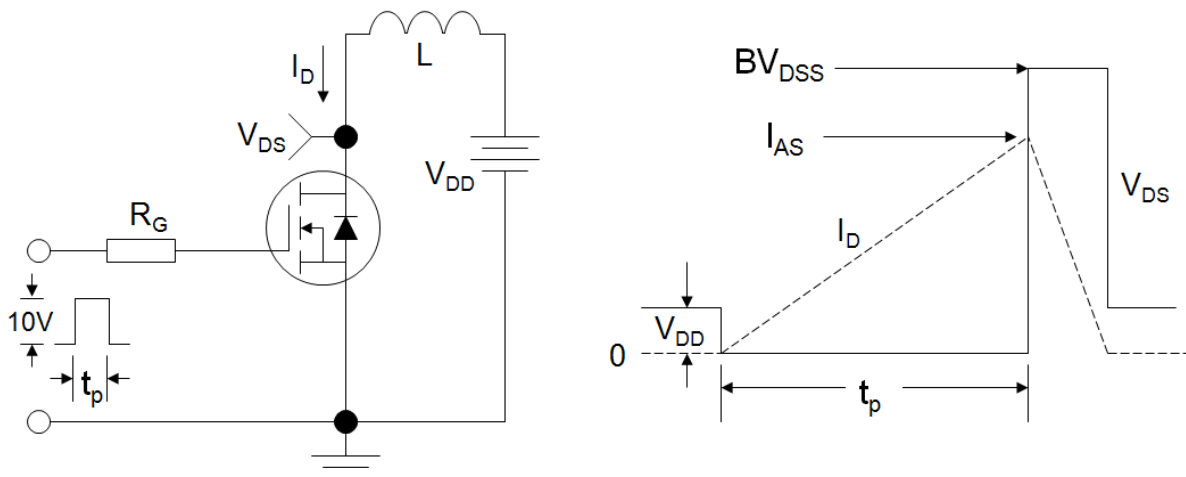
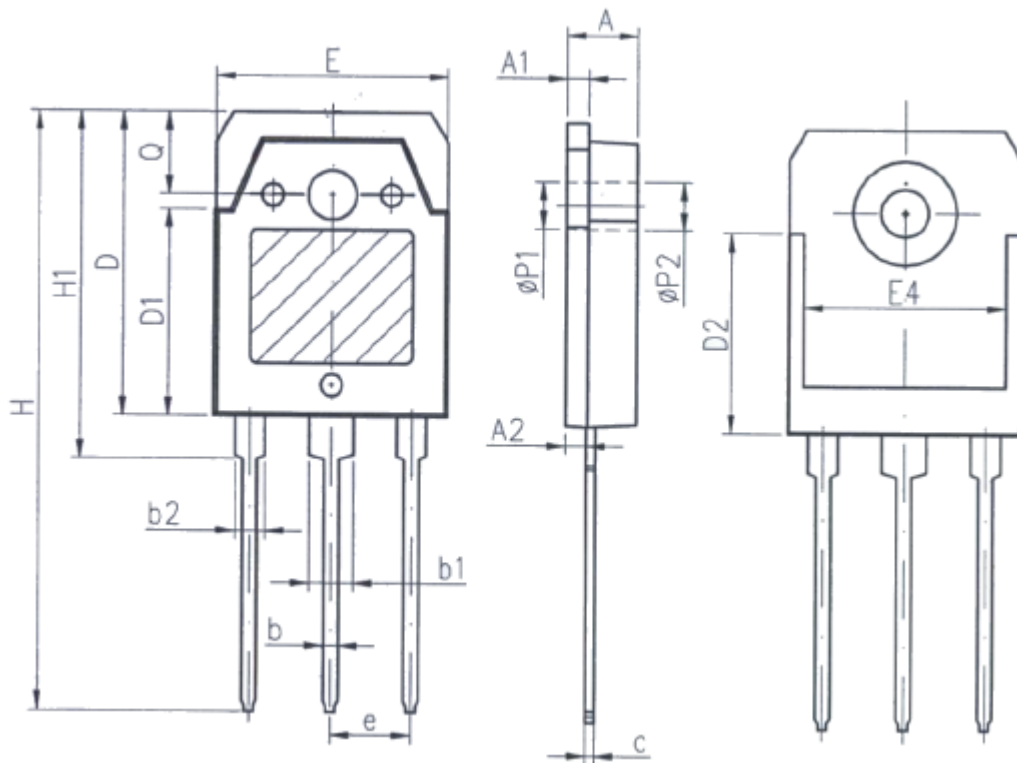


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





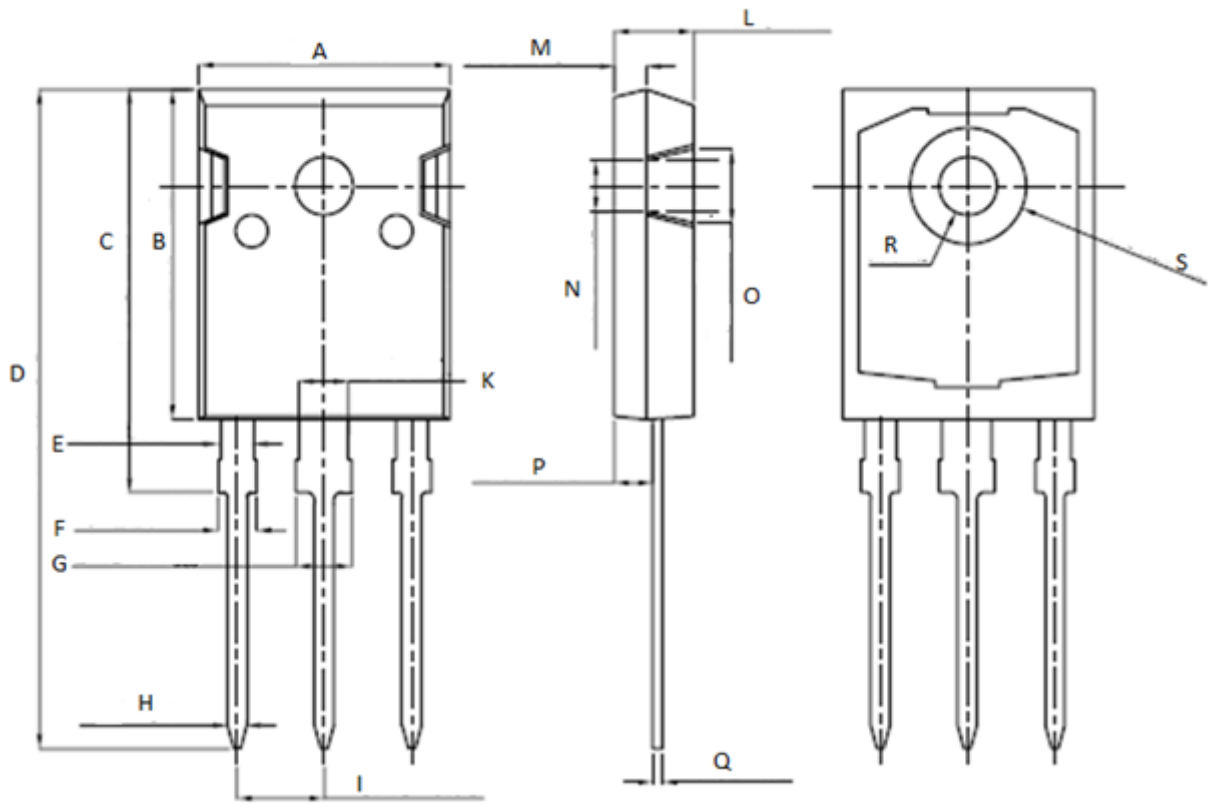
### TO-3PN



Unit:mm		
Symbol	Min.	Max.
A	4.6	5
A1	1.4	1.65
A2	1.18	1.58
b	0.8	1.2
b1	2.8	3.2
b2	1.8	2.2
c	0.5	0.75
D	19.6	20.2
D1	13.55	14.25
D2	12.9REF	
E	15.35	15.85
E4	12.6	-
e	5.45TYP	
H	40.1	40.9
H1	23.15	23.65
P1	3.2REF	
P2	3.5REF	



### TO-247



Unit: mm		
Symbol	Min.	Max.
A	15.95	16.25
B	20.85	21.25
C	20.95	21.35
D	40.5	40.9
E	1.9	2.1
F	2.1	2.25
G	3.1	3.25
H	1.1	1.3
I	5.40	5.50

Unit: mm		
Symbol	Min.	Max.
K	2.90	3.10
L	4.90	5.30
M	1.90	2.10
N	4.50	4.70
O	5.40	5.60
P	2.29	2.49
Q	0.51	0.71
R	φ 3.5	φ 3.7
S	φ 7.1	φ 7.3



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